

FUJI POWER MOSFET Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

($T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V_{DS}	200	V
	V_{DSX}^*5	170	V
Continuous drain current	I_D	± 18	A
Pulsed drain current	$I_{D(puls)}$	± 72	A
Gate-source voltage	V_{GS}	± 30	V
Non-repetitive Avalanche current	I_{AS}^*2	18	A
Maximum Avalanche Energy	E_{AS}^*1	125.5	mJ
Maximum Drain-Source dV/dt	dV_{DS}/dt^*4	20	kV/ μs
Peak Diode Recovery dV/dt	dV/dt^*3	5	kV/ μs
Max. power dissipation	P_D	$T_a=25^\circ\text{C}$	2.02
		$T_c=25^\circ\text{C}$	105
Operating and storage temperature range	T_{ch}	+150	$^\circ\text{C}$
	T_{stg}	-55 to +150	$^\circ\text{C}$

*1 $L=620\mu\text{H}$, $V_{CC}=48\text{V}$, $T_{ch}=25^\circ\text{C}$, See to Avalanche Energy Graph *2 $T_{ch} \leq 150^\circ\text{C}$

*3 $I_F \leq -I_D$, $-di/dt=50\text{A}/\mu\text{s}$, $V_{CC} \leq BV_{DSS}$, $T_{ch} \leq 150^\circ\text{C}$ *4 $V_{DS} \leq 200\text{V}$ *5 $V_{GS}=-30\text{V}$

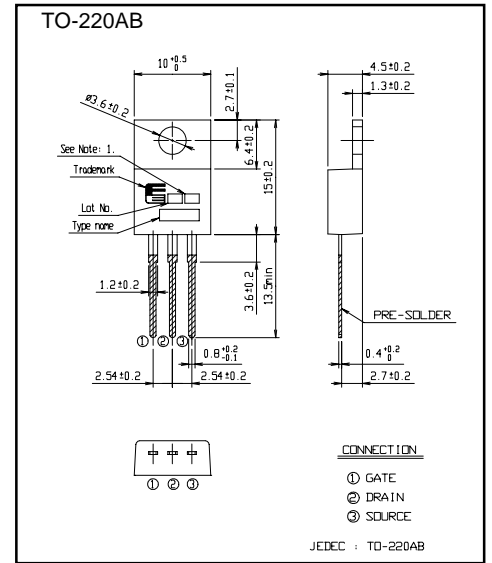
● **Electrical characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)**

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D=250\mu\text{A}$ $V_{GS}=0\text{V}$	200			V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ $V_{DS}=V_{GS}$	3.0		5.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=200\text{V}$ $V_{GS}=0\text{V}$			25	μA
		$V_{DS}=160\text{V}$ $V_{GS}=0\text{V}$			250	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 30\text{V}$ $V_{DS}=0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=6.5\text{A}$ $V_{GS}=10\text{V}$		131	170	$\text{m}\Omega$
Forward transconductance	g_{fs}	$I_D=6.5\text{A}$ $V_{DS}=25\text{V}$	5.5	11		S
Input capacitance	C_{iss}	$V_{DS}=75\text{V}$		770	1155	pF
Output capacitance	C_{oss}	$V_{GS}=0\text{V}$		110	165	pF
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$		5	7.5	pF
Turn-on time t_{on}	$t_{d(on)}$	$V_{CC}=48\text{V}$ $I_D=6.5\text{A}$		12	18	ns
	t_r	$V_{GS}=10\text{V}$		2.6	3.9	ns
Turn-off time t_{off}	$t_{d(off)}$	$R_{GS}=10\Omega$		22	33	ns
	t_f			6.1	9.2	ns
Total Gate Charge	Q_G	$V_{CC}=100\text{V}$		21	31.5	nC
Gate-Source Charge	Q_{GS}	$I_D=13\text{A}$		8	12	nC
Gate-Drain Charge	Q_{GD}	$V_{GS}=10\text{V}$		5	7.5	nC
Avalanche capability	I_{AV}	$L=620\mu\text{H}$ $T_{ch}=25^\circ\text{C}$	18			A
Diode forward on-voltage	V_{SD}	$I_F=13\text{A}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		1.10	1.65	V
Reverse recovery time	t_{rr}	$I_F=13\text{A}$ $V_{GS}=0\text{V}$		0.15		μs
Reverse recovery charge	Q_{rr}	$-di/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$		0.88		μC

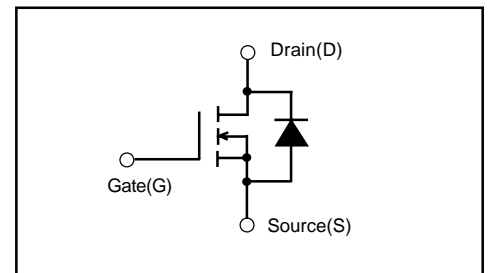
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			1.191	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$	channel to ambient			62.0	$^\circ\text{C}/\text{W}$

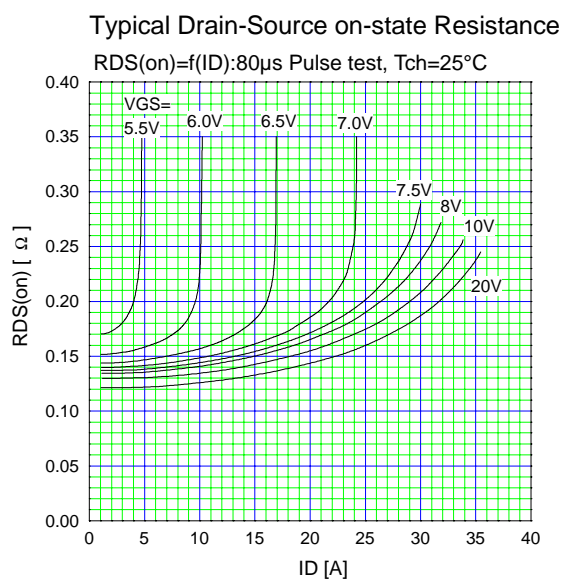
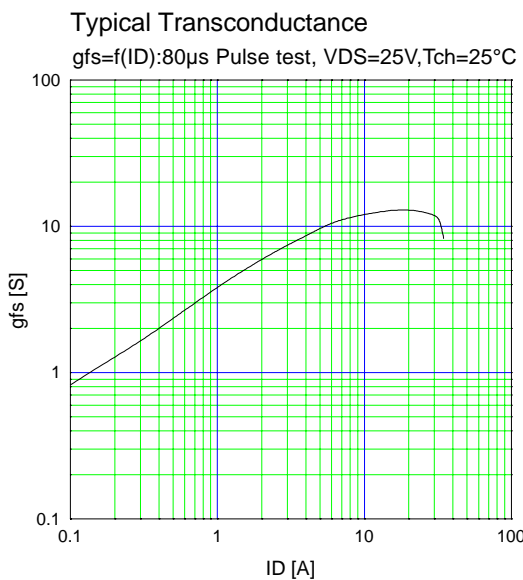
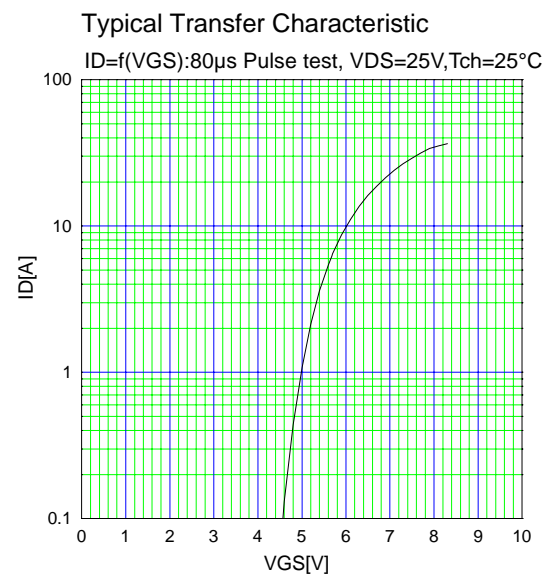
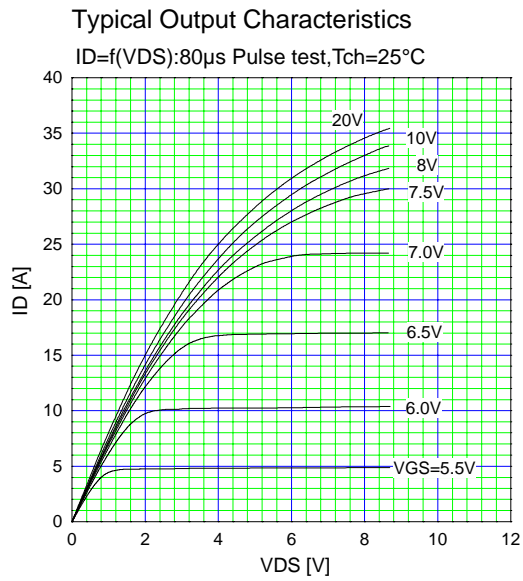
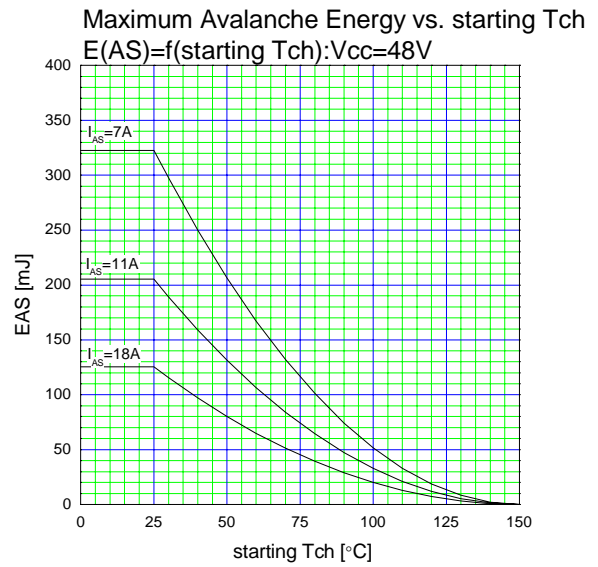
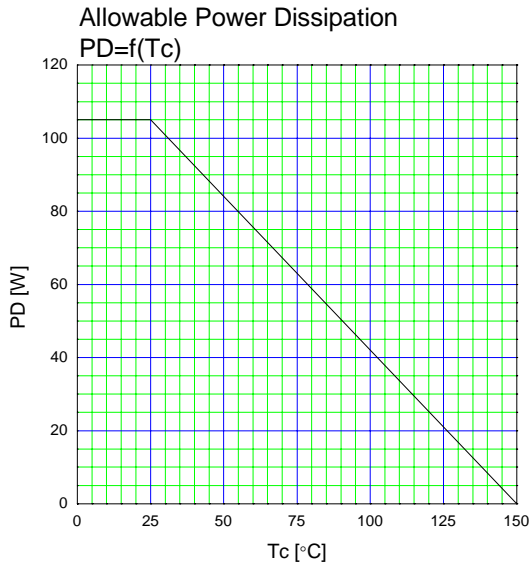
Outline Drawings (mm)



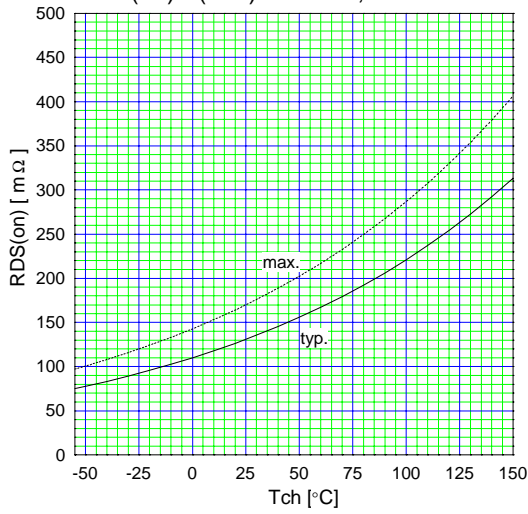
Equivalent circuit schematic



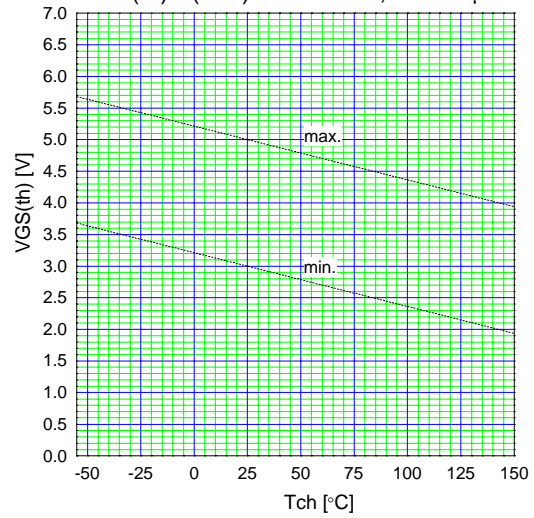
Characteristics



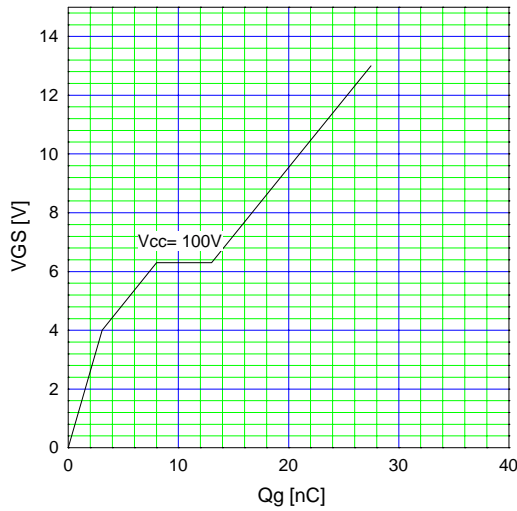
Drain-Source On-state Resistance
 $R_{DS(on)}=f(T_{ch}):I_D=6.5A, V_{GS}=10V$



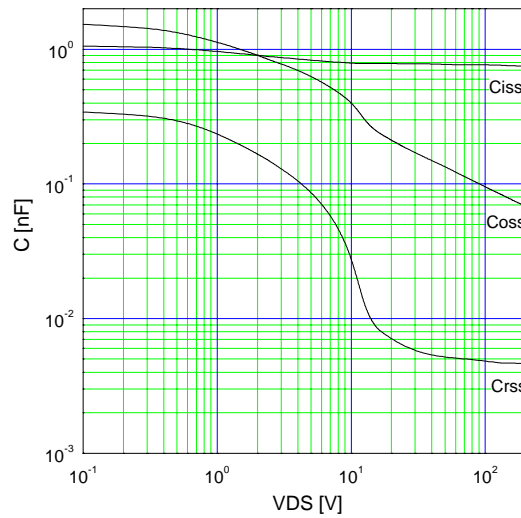
Gate Threshold Voltage vs. Tch
 $V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



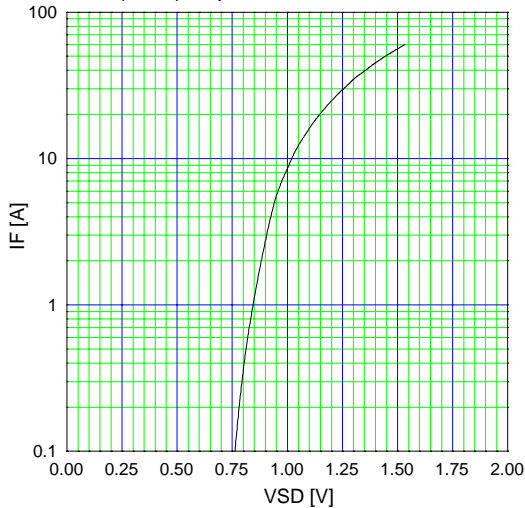
Typical Gate Charge Characteristics
 $V_{GS}=f(Q_g):I_D=13A, T_{ch}=25^\circ C$



Typical Capacitance
 $C=f(V_{DS}):V_{GS}=0V, f=1MHz$



Typical Forward Characteristics of Reverse Diode
 $I_F=f(V_{SD}):80\mu s$ Pulse test, $T_{ch}=25^\circ C$



Typical Switching Characteristics vs. ID
 $t=f(I_D):V_{CC}=48V, V_{GS}=10V, R_G=10\Omega$

